

isc Silicon NPN Darlington Power Transistor

2SC4574

DESCRIPTION

- Low Collector Saturation Voltage
- High DC Current Gain
- High Reliability

APPLICATIONS

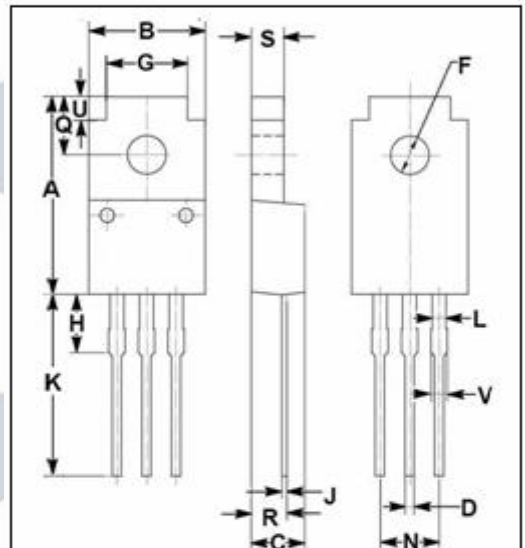
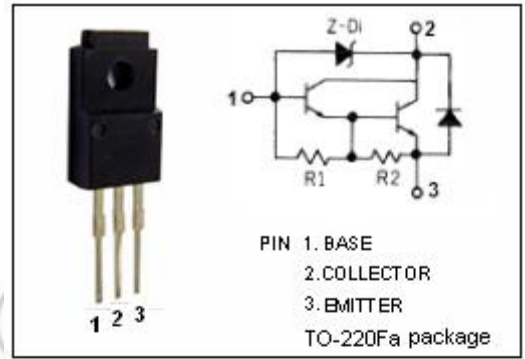
- General purpose power amplifiers
- Including zener diode

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	50-70	V
V _{CEO(SUS)}	Collector-Emitter Voltage	50-70	V
V _{EBO}	Emitter-Base Voltage	6	V
I _c	Collector Current-Continuous	4	A
P _c	Collector Power Dissipation @ T _c =25°C	30	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	4.5	°C/W



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

isc Silicon NPN Darlington Power Transistor**2SC4574****ELECTRICAL CHARACTERISTICS** **$T_c=25^\circ\text{C}$ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=50\mu\text{A}; I_E=0$	50		70	V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; I_B=0$	50		70	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1.5\text{A}; I_B=6\text{mA}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=40\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			3	mA
h_{FE}	DC Current Gain	$I_C=1.5\text{A}; V_{CE}=5\text{V}$	2000		10000	